

16384 BIT BIPOLAR TTL

PROGRAMMABLE READ ONLY MEMORY

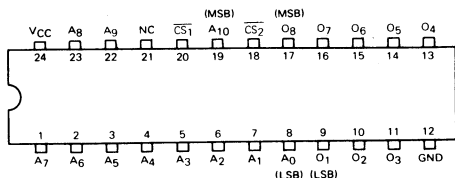
Description

The μPB419C and μPB419D are high speed, electrically programmable, fully decoded 16384 bit TTL read only memories. On-chip address decoding, two chip select inputs and three-state outputs allow easy expansion of memory capacity. The μPB419C and μPB419D are fabricated with logic level zero (low); logic level one (high) can be electrically programmed into the selected bit locations. The same address inputs are used for both programming and reading.

Features

- 2048 WORDS x 8 BITS organization (Fully decoded)
- TTL Interface
- Fast read access time : 50 ns MAX. (μPB419-2)
- Medium power consumption : 500 mW TYP.
- Two chip select inputs for memory expansion
- Three-state outputs
- Cerdip 24-Lead Dual In-Line Package (μPB419D)
- Plastic 24-Lead Dual In-Line Package (μPB419C)
- Fast Programming time : 200 μs/bit TYP.
- Replaceable with : Intel's 2716 and equivalent devices (as a ROM)

Connection Diagram (Top View)



Pin names

- A0 - A10 : Address Inputs
- O1 - O8 : Data Outputs
- CS1, CS2 : Chip Select Inputs
- NC : No Connection
- VCC : Power Supply (+5V)
- GND : Ground

Operation

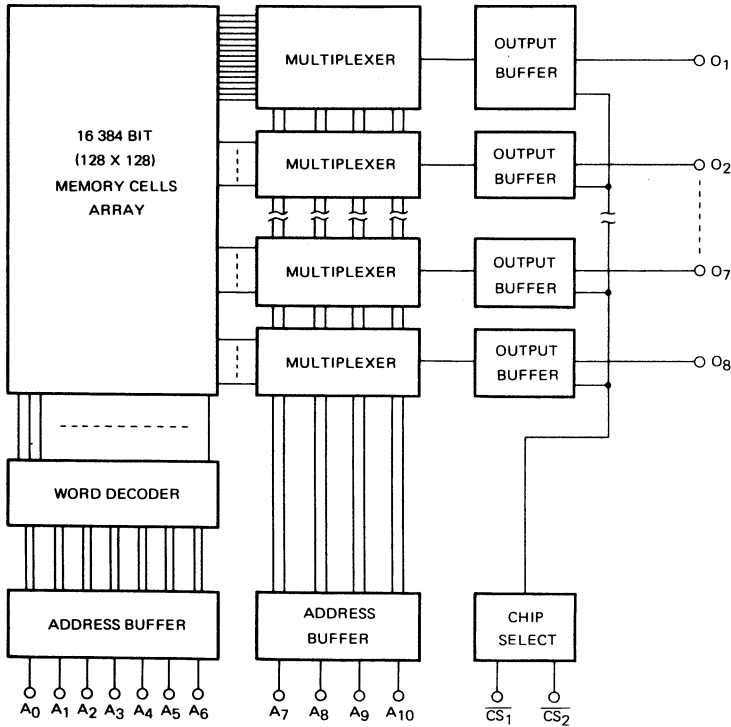
1. Programming

A logic one can be permanently programmed into a selected bit location by using special equipment (programmer). First, the desired word is selected by the eleven address inputs in TTL levels. Either or both of the two Chip Select inputs \overline{CS}_1 and \overline{CS}_2 should be at a logical one. Secondly, a train of high current programming pulses is applied to the desired output. After the sensed voltage indicates that the selected bit is in the logic one state, an additional pulse train is applied, then is stopped.

2. Reading

To read the memory, Both of the two Chip Select inputs must be held at a logical zero. The outputs then correspond to the data programmed in the selected words. When either or both of the two Chip Select inputs are at a logical one, all the outputs will be floating.

Logic Diagram



ABSOLUTE MAXIMUM RATINGS

Supply Voltage	V _{CC}	-0.5 to +7.0	V
Input Voltage	V _I	-0.5 to +5.5	V
Output Voltage	V _O	-0.5 to +5.5	V
Output Current	I _O	50	mA
Operating Temperature	T _{opt}	-25 to +75	°C
Storage Temperature			
Cerdip Package	T _{stg}	-65 to +150	°C
Plastic Package	T _{stg}	-55 to +125	°C

D.C. CHARACTERISTICS (V_{CC} = 4.5 to 5.5 V, T_a = 0 to +75 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Input High Voltage	V _{IH}	2.0			V	
Input Low Voltage	V _{IL}			0.85	V	
Input High Current	I _{IH}			40	μA	V _I =5.5 V V _{CC} =5.5 V
Input Low Current	-I _{IL}			0.25	mA	V _I =0.4 V V _{CC} =5.5 V
Output Low Voltage	V _{OL}			0.45	V	I _O =16 mA V _{CC} =4.5 V
Output Leakage Current	I _{OFF1}			40	μA	V _O =5.5 V V _{CC} =5.5 V
Output Leakage Current	-I _{OFF2}			40	μA	V _O =0.4 V V _{CC} =5.5 V
Input Clamp Voltage	-V _{IC}			1.2	V	I _I =-18 mA V _{CC} =4.5 V
Power Supply Current	I _{CC}		100	160	mA	All Inputs Grounded, V _{CC} =5.5 V
Output High Voltage	V _{OH}	2.4			V	I _O =-2.4 mA V _{CC} =4.5 V
Output Short Circuit Current	-I _{SC}	20		70	mA	V _O =0 V

CAPACITANCE (V_{CC} = 5 V, f = 1 MHz, T_a = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	MAX.	UNIT	TEST CONDITIONS
Input Capacitance	C _{IN}		8	pF	V _{IN} = 2.5 V
Output Capacitance	C _{OUT}		10	pF	V _{OUT} = 2.5 V

A.C. CHARACTERISTICS (V_{CC} = 4.5 to 5.5 V, T_a = 0 to +75 °C)

CHARACTERISTIC	SYMBOL	μPB419C-2 μPB419D-2		μPB419C-1 μPB419D-1		μPB419C μPB419D		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Address Access Time	t _{AA}		50		60		70	ns
Chip Select Access Time	t _{ACS}		30		40		50	ns
Chip Select Disable Time	t _{DCS}		30		40		50	ns

Note 1. Output Load: See Fig. 1.

Note 2. Input Waveform: 0.0 V for low level and 3.0 V for high level, less than 10 ns for both rise and fall times.

Note 3. Measurement References: 1.5 V for both inputs and outputs.

Note 4. C_L in Fig. 1 includes jig and probe stray capacitances.

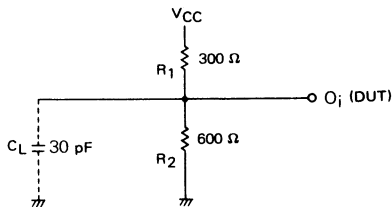


Fig. 1

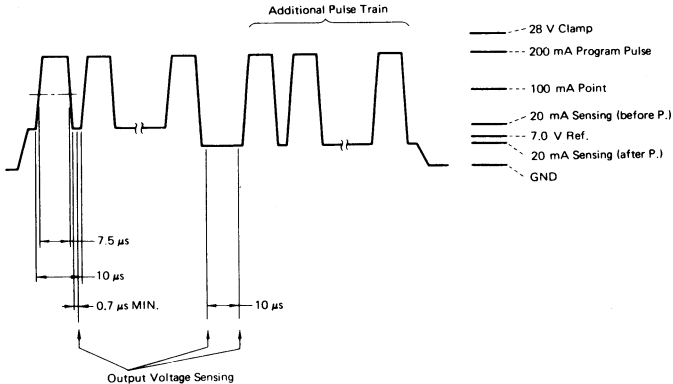
Programming Specification

It is imperative that this specification be rigorously observed in order to correctly program the μPB419C and μPB419D. NEC will not accept responsibility for any device found to be defective if it were not programmed according to this specification.

CHARACTERISTIC	LIMIT	UNIT	NOTES
Ambient Temperature	25 ±5	°C	
Programming Pulse Amplitude Clamp Voltage Ramp Rate (Both in Rise and in Fall) Pulse Width Duty Cycle	200 ±5 % 28 +0 % -2 % 70 MAX. 7.5 ±5 % 70 % MIN.	mA V V/μs μs	15 V point/150 Ω load.
Sense Current Amplitude Clamp Voltage Ramp Rate Sense Current Interruption before and after address change	20 ±0.5 28 +0 % -2 % 70 MAX. 10 MIN.	mA V V/μs μs	15 V point/150 Ω load.
Programming V _{CC}	5.0 +5 % -0 %	V	
Maximum Sensed Voltage* for programmed "1"	7.0 ±0.1	V	
Delay from trailing edge of programming pulse before sensing output voltage	0.7 MIN.	μs	

* A bit is judged to be programmed when two successive sense readings 10 μs apart with no intervening programming pulse, pass the limit. When this condition has been met, four additional pulses are applied and the pulse train, then the sense current is terminated.

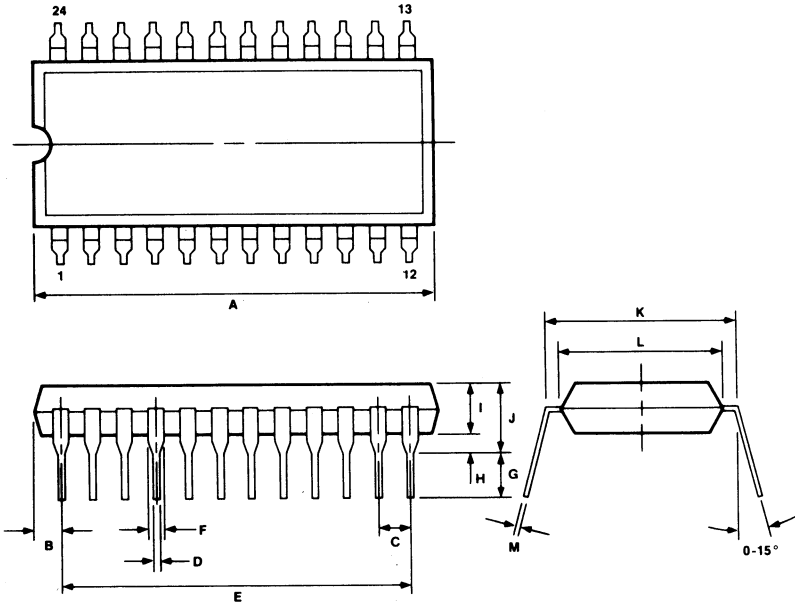
Fig. 2 Typical Output Voltage Waveform.



Package Dimensions

24PIN Plastic DIP

Item	Millimeters
A	33.02 max
B	2.54 max
C	2.54 [TP]
D	.50 ± .10
E	27.94
F	1.2 min
G	3.5 ± 0.3
H	.51 min
I	4.31 max
J	5.72 max
K	15.24 [TP]
L	13.2
M	+ .10 - .05



24PIN Cerdip

Item	Millimeters
A	33.02 max
B	2.54 max
C	2.54 [TP]
D	.50 ± .010
E	27.94
F	1.2 min
G	3.0 ± .3
H	.51 min
I	3.80
J	5.08 max
K	15.24 [TP]
L	13.21
M	.25 ± .05

